

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)

2. (Currently Amended) ~~The method of forming a ferroelectric film as defined in claim 1, wherein:~~

~~the alloy film is formed in an inert gas atmosphere; and~~

~~supply of an oxidizing gas is started together with the supply of Ti. A method of forming a ferroelectric film including a complex oxide of lead zirconate titanate (PZT)~~

~~family on a metal film formed of platinum (Pt) by using a metalorganic chemical vapor deposition method, the method comprising:~~

~~starting supply of lead (Pb) to form an alloy film of Pb and Pt on the metal film, the alloy film being formed in an inert gas atmosphere;~~

~~starting supply of titanium (Ti) and an oxidizing gas at the same time to form initial crystal nuclei of a lead titanate (PbTiO₃) on the alloy film; and~~

~~starting supply of zirconium (Zr) to form a crystal grown layer of the complex oxide of PZT family on the initial crystal nuclei.~~

3. (Currently Amended) ~~The method of forming a ferroelectric film as defined in claim 1,~~

~~wherein the alloy film is formed at 400°C or less. A method of forming a ferroelectric film including a complex oxide of lead zirconate titanate (PZT) family on a metal film formed of platinum (Pt) by using a metalorganic chemical vapor deposition method, the method comprising:~~

~~starting supply of lead (Pb) to form an alloy film of Pb and Pt on the metal film, the alloy film is formed at about 150°C;~~

starting supply of titanium (Ti) to form initial crystal nuclei of a lead titanate (PbTiO₃) on the alloy film; and

starting supply of zirconium (Zr) to form a crystal grown layer of the complex oxide of PZT family on the initial crystal nuclei.

4. (Currently Amended) The method of forming a ferroelectric film as defined in ~~claim 1~~claim 2,

wherein the initial crystal nuclei arebeing formed in an island pattern.

5. (New) A method of forming a ferroelectric film including a complex oxide of lead zirconate titanate (PZT) family on a metal film formed of platinum (Pt) by using a metalorganic chemical vapor deposition method, the method comprising:

forming an alloy film of Pb and Pt on the metal film, the alloy film being formed in an inert gas atmosphere;

form initial crystal nuclei of a lead titanate (PbTiO₃) on the alloy film in an oxidizing gas atmosphere; and

forming a crystal grown layer of the complex oxide of PZT family on the initial crystal nuclei.

6. (New) A method of forming a ferroelectric film including a complex oxide of lead zirconate titanate (PZT) family on a metal film formed of platinum (Pt) by using a metalorganic chemical vapor deposition method, the method comprising:

forming an alloy film of Pb and Pt on the metal film at about 150°C;

forming initial crystal nuclei of a lead titanate (PbTiO₃) on the alloy film; and

forming a crystal grown layer of the complex oxide of PZT family on the initial crystal nuclei.

7. (New) The method of forming a ferroelectric film as defined in claim 3, wherein the initial crystal nuclei arebeing formed in an island pattern.